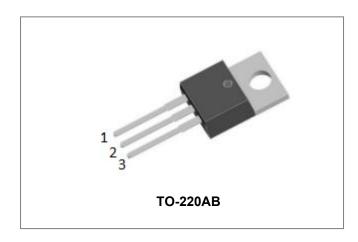






MBR2045CTP SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V_{RRM}	-		
Working Peak Reverse Voltage	V_{RWM}		45	V
DC Blocking Voltage	V_R			
Average Destified Femyard Current		50% duty cycle @Tc=116°C,	10(Per Leg)	^
Average Rectified Forward Current	I _F (AV)	rectangular wave form	20(Per Device)	А
Peak One Cycle Non-Repetitive Surge	I _{FSM}	8.3ms, Half Sine pulse	150	Α
Current(Per Leg)	IF5M	0.0113, Flair Offic pulse	100	

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (per leg) *	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.57 0.74	- 0.84	٧
(per leg)	V _{F2}	@ 20A, Pulse, T _J = 25 °C @ 10A, Pulse, T _J = 125 °C	0.74	-	\ /
		@ 20A, Pulse, T _J = 125 °C	0.70	0.72	V
Reverse Current (per leg) *	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.03	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	9	15.0	mA
Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	250	400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

Pulse width < 300 µs, duty cycle < 2%

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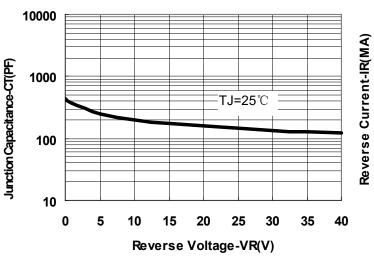




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _{th(j-c)}	DC operation	5	°C/W
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			

Ratings and Characteristics Curves



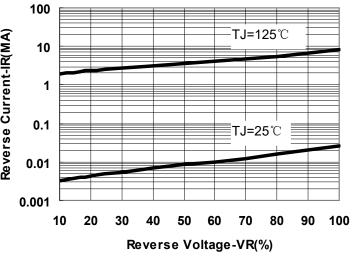


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

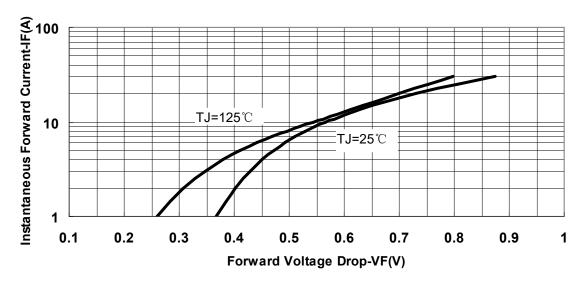


Fig.3-Typical Instantaneous Forward Voltage Characteristics

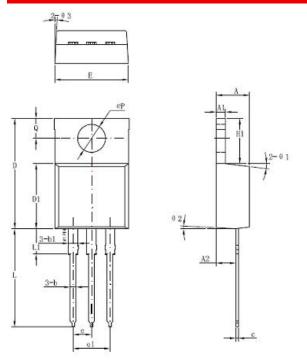
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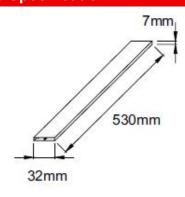


Mechanical Dimensions TO-220AB

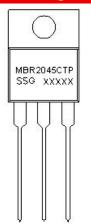


Symbol	Dimensions in millimeters			
	Min	Typical	Max	
Α	3.56	-	4.83	
A1	0.51	-	1.40	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
С	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E	9.65	-	10.67	
е	-	2.54	-	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.70	-	14.73	
L1	-	-	6.35	
ФР	-	3.56	-	
Q	2.54	-	3.43	

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

 MBR
 = Device Type

 20
 = Forward Current (20A)

 45
 = Reverse Voltage(45V)

 CTP
 = Configuration

 SSG
 = SSG

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
MBR2045CTP	TO-220AB (Pb-Free)	50 pcs/ tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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